

AlGaAs laser diodes

RLD-78MIT / RLD-78PIT / RLD-78NIT

The RLD-78MIT, RLD-78PIT and RLD-78NIT are the world's first mass-produced laser diodes those are manufactured by molecular beam epitaxy. Modal noise is controlled by relaxation oscillation, and they are ideal for short-distance, high-speed optical communications.

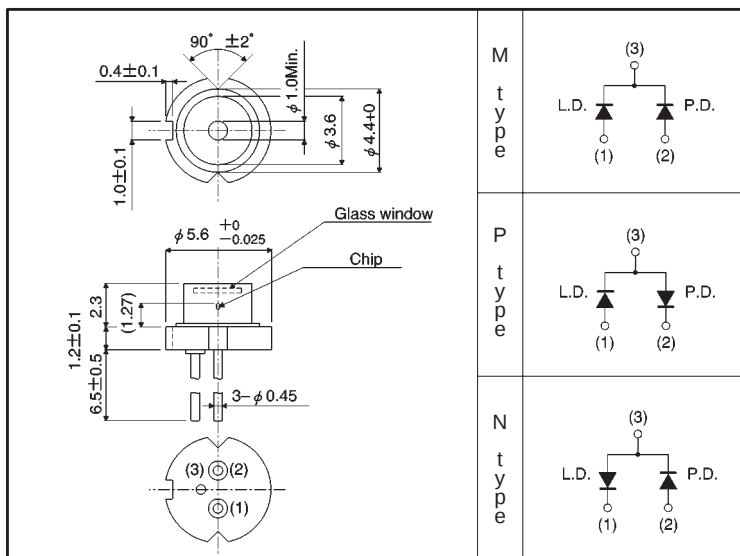
●Applications

Short-distance optical communications

●Features

- 1) High oscillation relaxation frequency.
- 2) Little transmission loss within optical fiber.
- 3) High-precision, compact package.
- 4) Little dispersion of characteristics.
- 5) Long life.
- 6) Can be driven by single power supply (P and N types).

●External dimensions (Units: mm)



●Absolute maximum ratings (Tc = 25°C)

Parameter		Symbol	Limits	Unit
Output		Po	5	mW
Reverse voltage	Laser	VR	2	V
	PIN photodiode	VR (PIN)	30	V
Operating temperature		Topr	-10~+80	°C
Storage temperature		Tstg	-40~+90	°C

●Electrical and optical characteristics (Tc = 25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Threshold current	I _{th}	—	35	50	mA	—
Operating current	I _{op}	—	45	65	mA	P _o =3mW
Operating voltage	V _{op}	—	1.9	2.3	V	P _o =3mW
Differential efficiency	η	0.1	0.25	0.6	mW / mA	$\frac{2\text{mW}}{I(3\text{mW}) - I(1\text{mW})}$
Monitor current	I _m	0.1	0.2	0.6	mA	P _o =3mW, V _{R(PIN)} =15V
Parallel divergence angle	θ _∥ *	8	11	15	deg	P _o =3mW
Perpendicular divergence angle	θ _⊥ *	28	37	45	deg	
Parallel deviation angle	Δφ _∥	—	—	±2	deg	
Perpendicular deviation angle	Δφ _⊥	—	—	±3	deg	
Emission point accuracy	$\begin{matrix} \Delta X \\ \Delta Y \\ \Delta Z \end{matrix}$	—	—	±80	μm	—
Peak emission wavelength	λ	770	785	810	nm	P _o =3mW
Relaxation oscillation frequency	f _r	1.8	—	—	GHz	P _{ave} =1.5mV, 50%duty

* θ_∥ and θ_⊥ are defined as the angle within which the intensity is 50% of the peak value.

●Electrical and optical characteristic curves

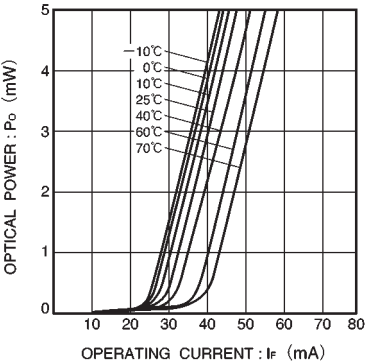


Fig. 1 Optical output vs. operating current

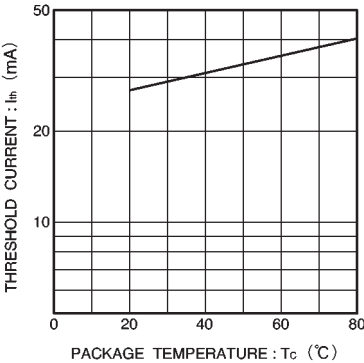


Fig. 2 Dependence of threshold current on temperature

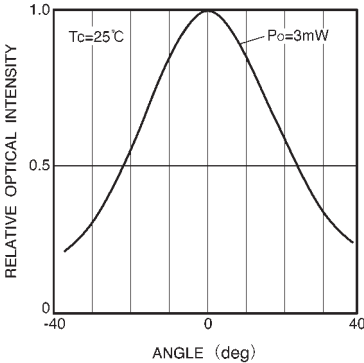


Fig. 3 Perpendicular far field pattern

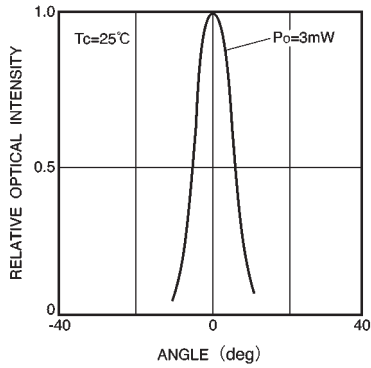


Fig. 4 Parallel far field pattern

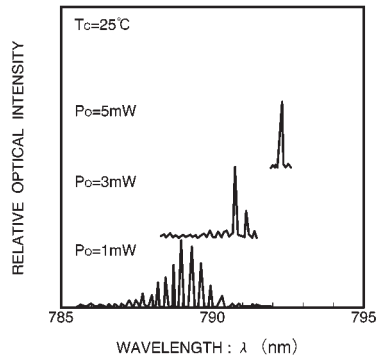


Fig. 5 Dependence of emission spectrum on optical output

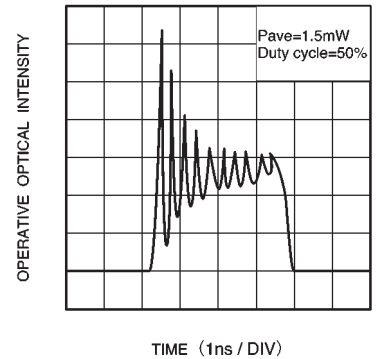


Fig. 6 Pulse response characteristic

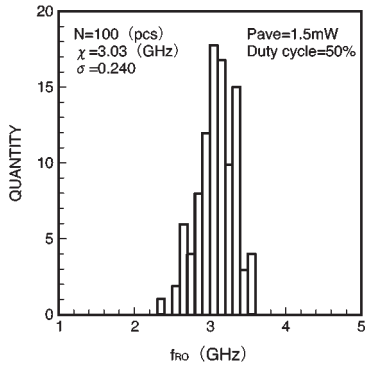


Fig. 7 Distribution of relaxation oscillation frequency